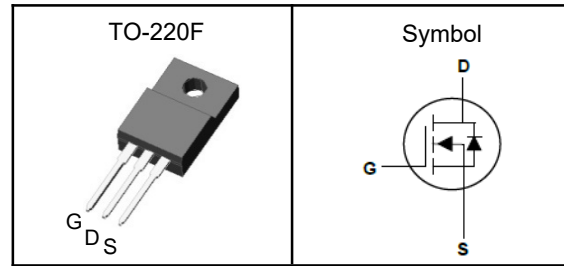


700V Super Junction Power MOSFET
Features

- Low drain-source on-resistance: $R_{DS(ON)}=0.33\Omega(\text{typ})$
- Easy to control gate switching
- Enhancement mode: $V_{th} = 2.5$ to $4.5V$
- 100% avalanche tested
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting

Pin Description


V_{DSS}	700	V
$R_{DS(ON)-Typ}$	330	m Ω
I_D	11	A

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DSS}	Drain-Source Voltage	700	V
V_{GSS}	Gate-Source Voltage	± 30	V
T_J	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy ³	140	mJ
$I_{DM}^{①}$	Pulse Drain Current Tested	33	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	W

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62.5	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4.1	$^\circ\text{C/W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C .

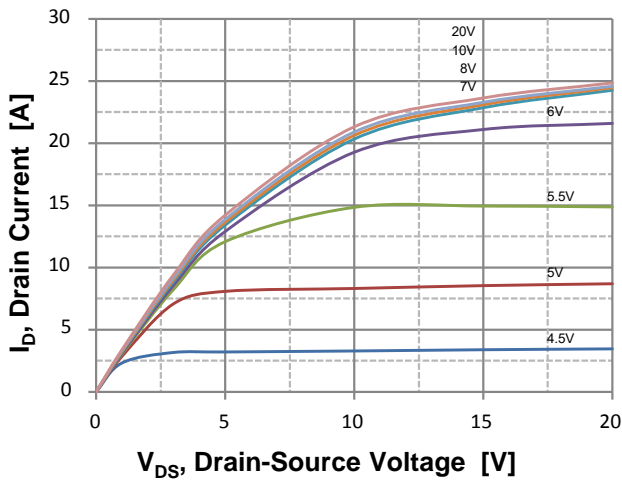
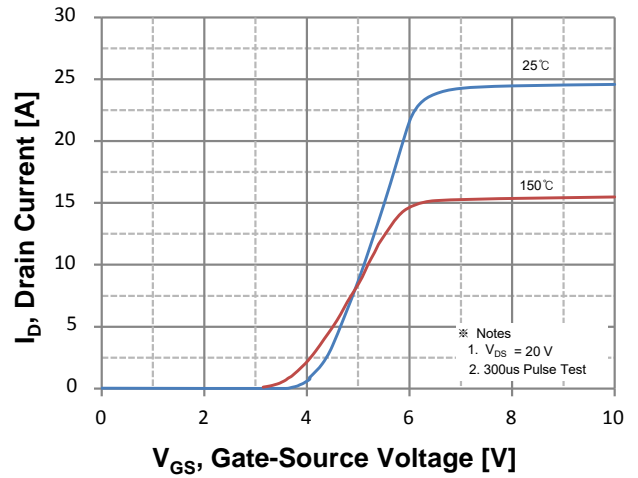
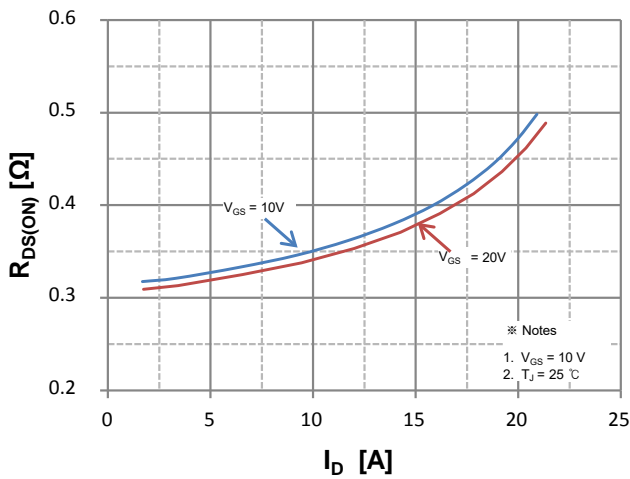
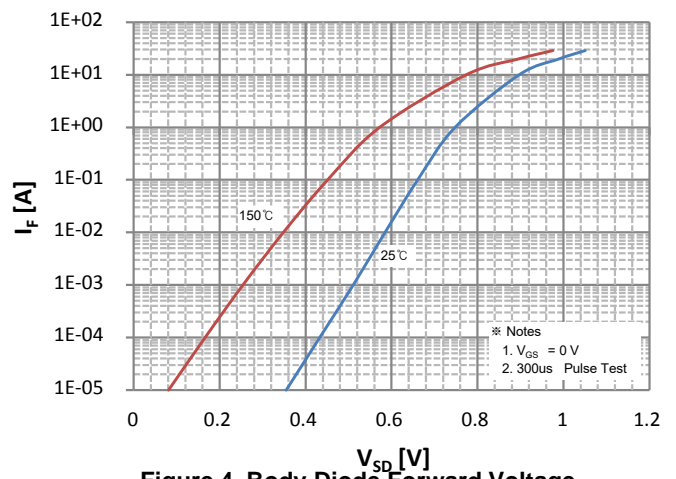
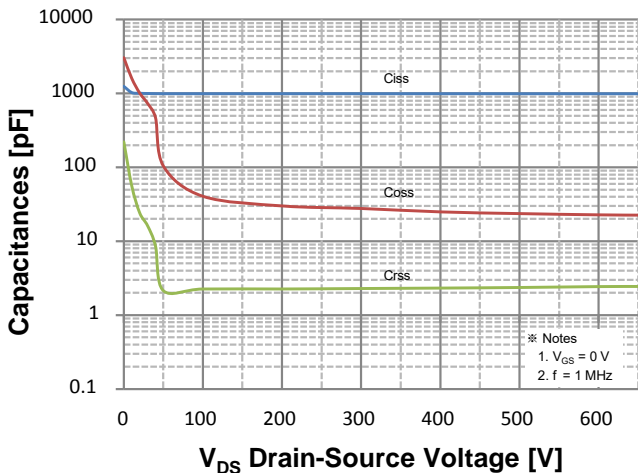
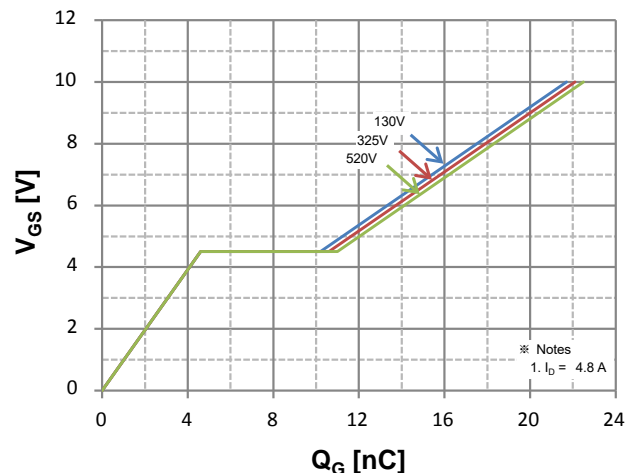
Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz.

**700V Super Junction Power MOSFET****Electrical Characteristics** ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	700	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=700V, V_{GS}=0V$	---	---	1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=370\mu A$	2.5	---	4.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=3.4A$	---	330	380	$m\Omega$
Dynamic Characteristics ^⑤						
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=100V,$ Freq.=1MHz	---	993	---	pF
C_{oss}	Output Capacitance		---	40	---	
C_{rss}	Reverse Transfer Capacitance		---	2.3	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, R_G=25\Omega,$ $I_D=4.8A$	---	30	---	nS
T_r	Turn-on Rise Time		---	23	---	
$T_{d(off)}$	Turn-off Delay Time		---	190	---	
T_f	Turn-off Fall Time		---	20	---	
Q_g	Total Gate Charge	$V_{DD}=520V, V_{GS}=10V,$ $I_D=4.8A$	---	22.6	---	nC
Q_{gs}	Gate-Source Charge		---	4.6	---	
Q_{gd}	Gate-Drain Charge		---	6.4	---	
Source-Drain Characteristics ($T_J=25^\circ\text{C}$)						
V_{SD}	Diode Forward Voltage _z	$V_{GS}=0V,$ $I_S=4.8A, T_J=25^\circ\text{C}$	---	---	1.3	V
t_{rr}	Reverse Recovery Time	$V_G=0V, I_S=4.8A,$ $di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	240	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.1	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

700V Super Junction Power MOSFET

Figure 1. On Region Characteristics

Figure 2. Transfer Characteristics

Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

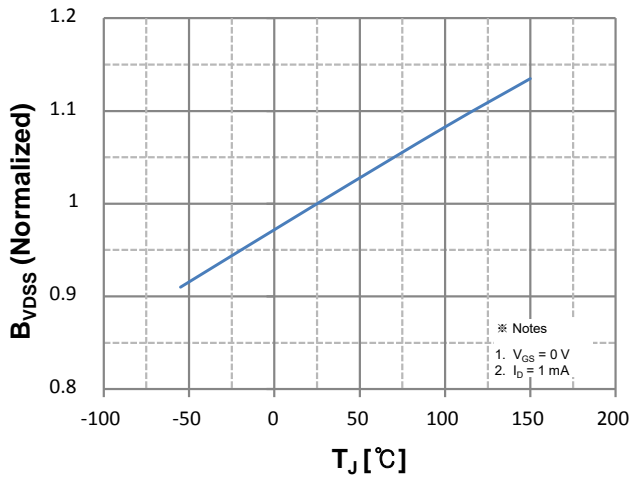
700V Super Junction Power MOSFET


Figure 7. Breakdown Voltage Variation vs. Temperature

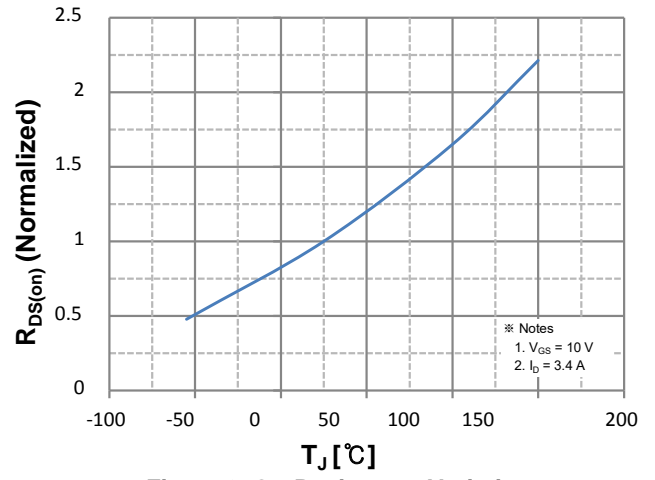


Figure 8. On-Resistance Variation vs. Temperature

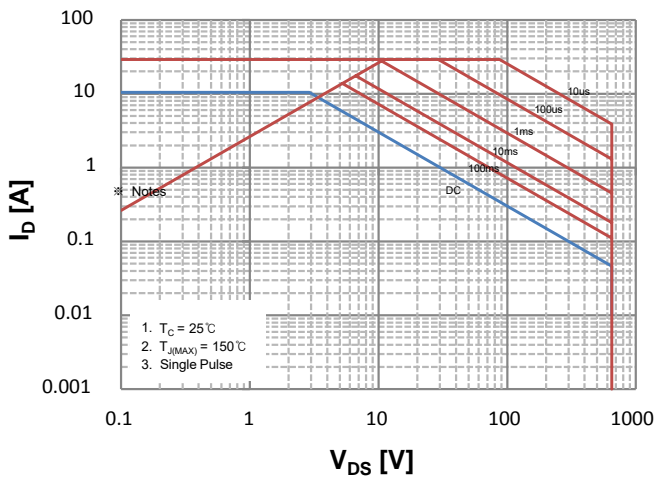


Figure 9. Maximum Safe Operating Area

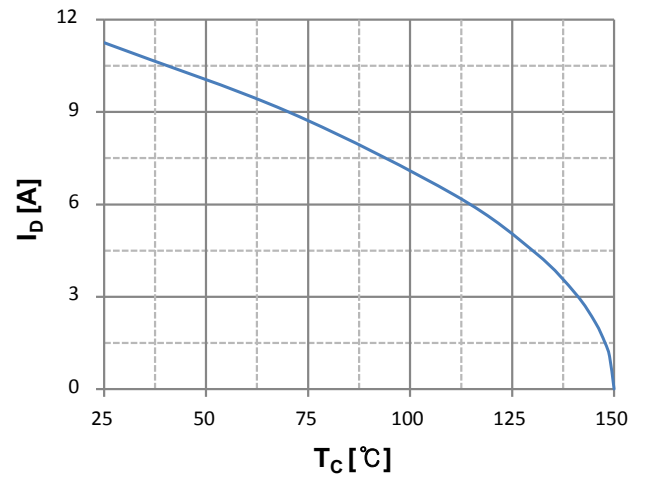


Figure 10. Maximum Drain Current vs. Case Temperature

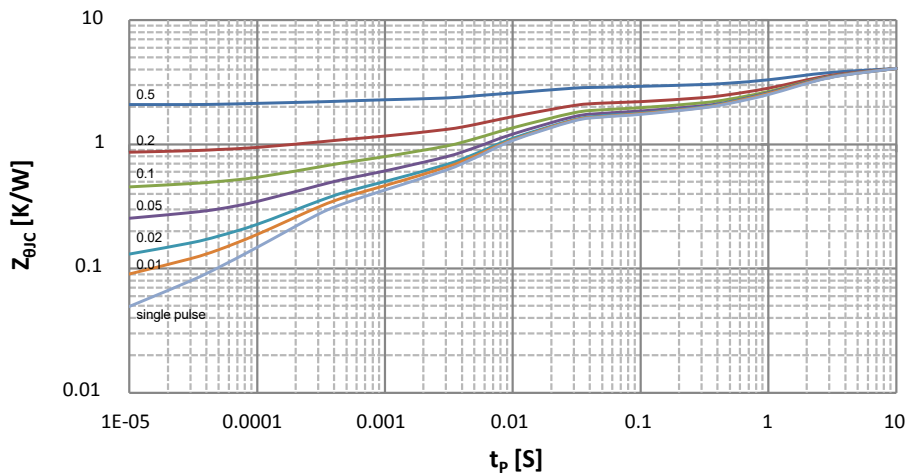


Figure 11. Transient Thermal Response Curve

700V Super Junction Power MOSFET
TO-220F Package Outline Data
